

SANYO	No.3008	2SC4364
		NPN Epitaxial Planar Silicon Transistor

VHF. UHF/MIX. OSC. Low-Voltage
High-Frequency Amp Applications

Features

- Low-voltage operation : $f_T = 3.0\text{GHz typ (}V_{CE} = 3\text{V)}$
- : $\text{MAG} = 11\text{dB typ (}V_{CE} = 3\text{V, }I_C = 3\text{mA)}$
- : $\text{NF} = 3.0\text{dB typ (}V_{CE} = 3\text{V, }I_C = 3\text{mA)}$

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

		unit
Collector to Base Voltage	V_{CB0}	25 V
Collector to Emitter Voltage	V_{CEO}	15 V
Emitter to Base Voltage	V_{EBO}	3 V
Collector Current	I_C	30 mA
Collector Dissipation	P_C	250 mW
Junction Temperature	T_j	150 $^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150 $^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

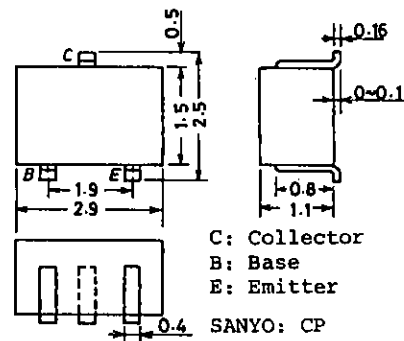
			min	typ	max	unit
Collector Cutoff Current	I_{CB0}	$V_{CB} = 15\text{V, }I_E = 0$			1.0	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 2\text{V, }I_C = 0$			1.0	μA
DC Current Gain	h_{FE}	$V_{CE} = 3\text{V, }I_C = 3\text{mA}$	40*		200*	
Gain-Bandwidth Product	f_T	$V_{CE} = 3\text{V, }I_C = 3\text{mA}$		3.0		GHz
Output Capacitance	c_{ob}	$V_{CB} = 3\text{V, }f = 1\text{MHz}$	0.75		1.3	pF
Reverse Transfer Capacitance	c_{re}	$V_{CB} = 3\text{V, }f = 1\text{MHz}$	0.7			pF
Forward Transfer Gain	$IS21eI^2$	$V_{CE} = 3\text{V, }I_C = 3\text{mA, }f = 0.9\text{GHz}$		7		dB
Maximum Available Power Gain	MAG	$V_{CE} = 3\text{V, }I_C = 3\text{mA, }f = 0.9\text{GHz}$		11		dB
Noise Figure	NF	$V_{CE} = 3\text{V, }I_C = 3\text{mA, }f = 0.9\text{GHz}$	3.0		5.0	dB

* The 2SC4364 is classified by 3mA h_{FE} as follows:

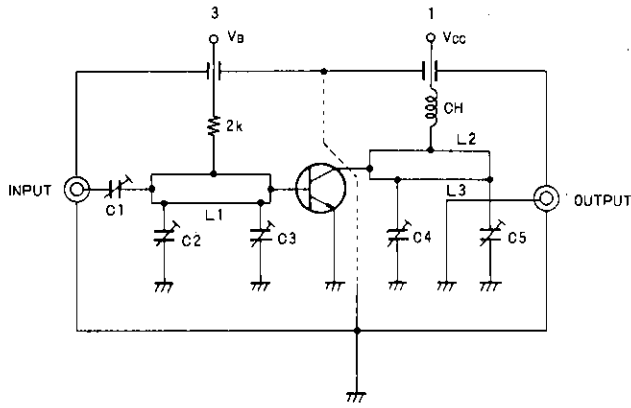
40	2	80	60	3	120	100	4	200
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(Note) Marking: OT
h_{FE} rank: 2,3,4

Package Dimensions 2018A
(unit: mm)

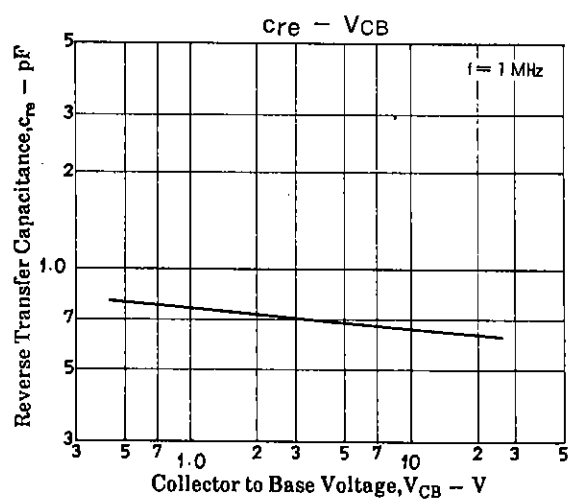
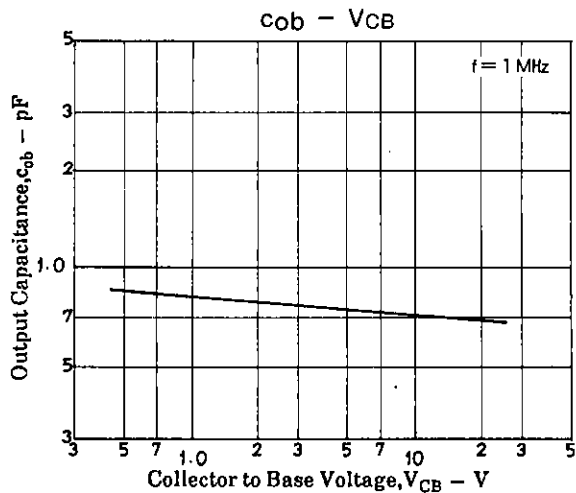
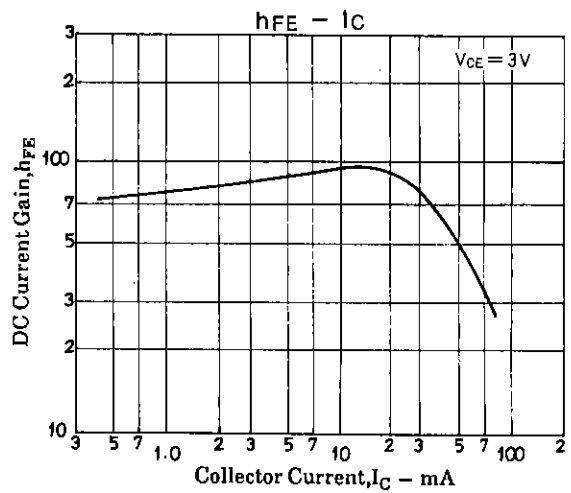
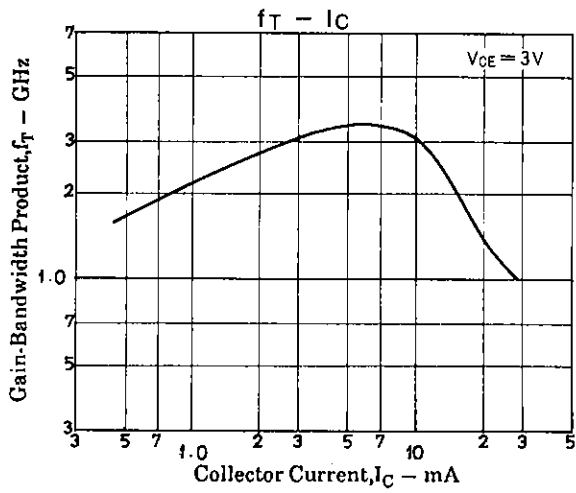


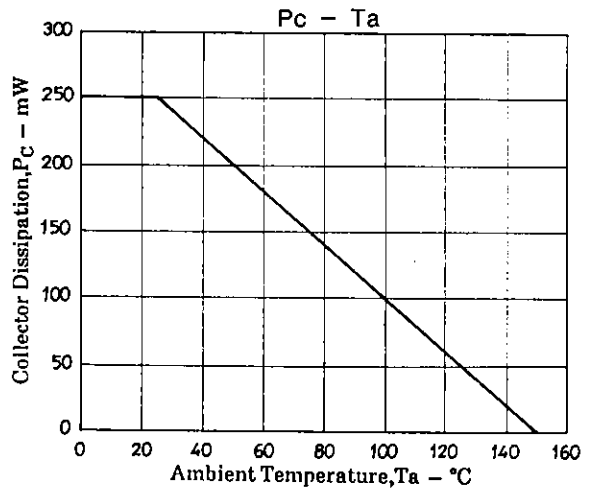
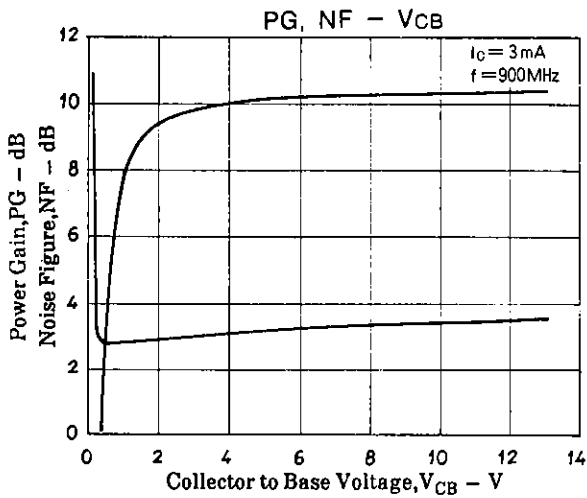
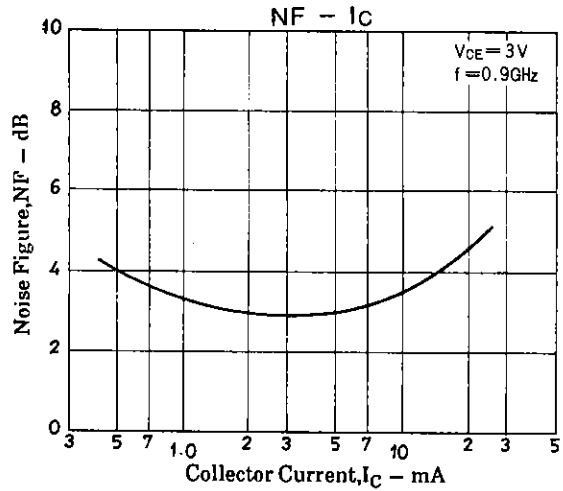
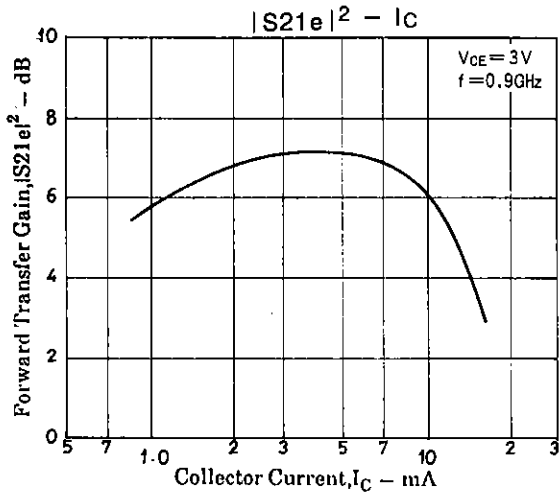
NF Test Circuit



900MHz	
C1	~ 5 pF
C2	~ 10 pF
C3	~ 10 pF
C4	~ 10 pF
C5	~ 10 pF
L1	W = 1.5mm, l = 25mm strip line
L2	W = 4mm, l = 25mm strip line
L3	0.5φ, l = 40mm
CH	2t + bead core

Unit (Resistance : Ω)





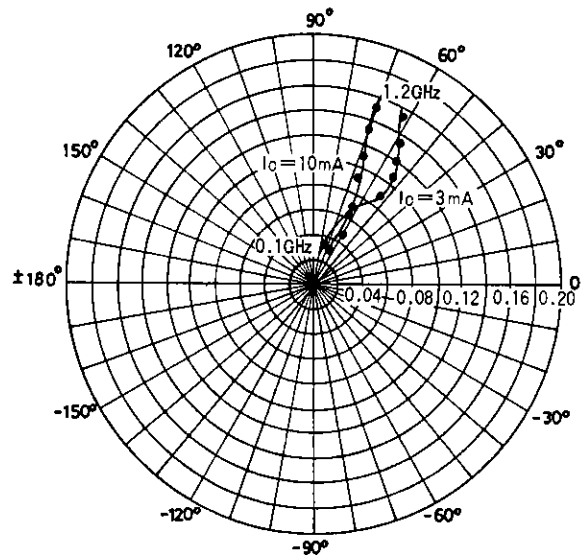
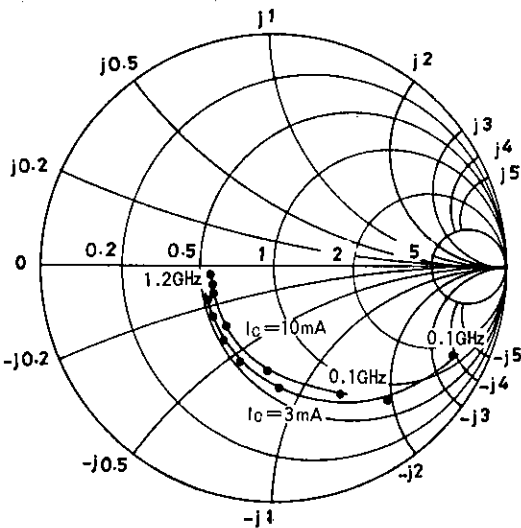
S parameter

S11e : $V_{CE} = 3V$

$f = 100MHz, 200 \sim 1200MHz (200MHz \text{ step})$

S12e : $V_{CE} = 3V$

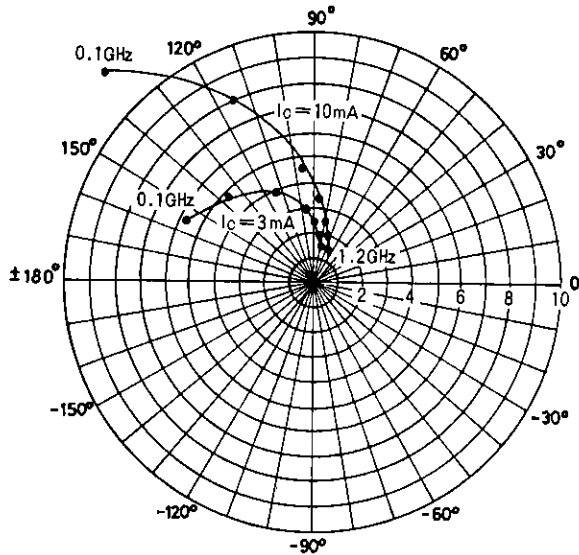
$f = 100MHz, 200 \sim 1200MHz (200MHz \text{ step})$



2SC4364

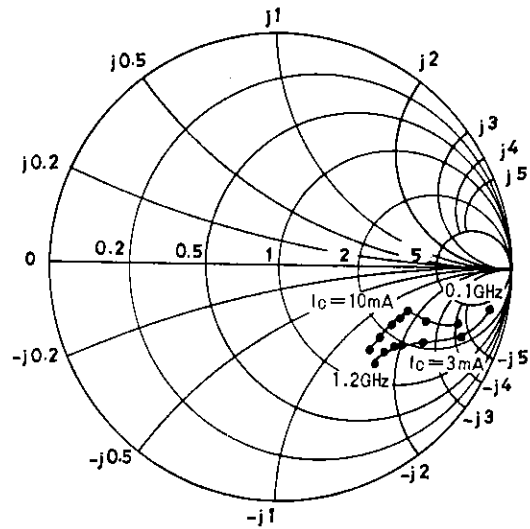
S21e : $V_{CE} = 3\text{ V}$

$f = 100\text{ MHz}$, 200~1200MHz (200MHz step)



S22e : $V_{CE} = 10\text{ V}$

$f = 100\text{ MHz}$, 200~1200MHz (200MHz step)



S parameter (Common emitter)

$V_{CE} = 3\text{ V}$, $I_C = 3\text{ mA}$, $Z_0 = 50\Omega$

Freq (MHz)	$ S_{11} $	$\angle S_{11}$	$ S_{21} $	$\angle S_{21}$	$ S_{12} $	$\angle S_{12}$	$ S_{22} $	$\angle S_{22}$
100	0.874	-25.4	5.638	154.7	0.036	73.4	0.931	-12.4
200	0.758	-46.8	4.895	137.3	0.061	62.3	0.842	-19.9
400	0.555	-85.9	3.925	112.5	0.088	53.7	0.696	-26.7
600	0.437	-110.1	3.004	97.1	0.105	53.2	0.631	-30.3
800	0.377	-127.8	2.387	86.7	0.119	56.2	0.596	-32.9
900	0.361	-135.3	2.201	82.7	0.128	57.3	0.594	-34.4
1000	0.353	-141.9	2.014	79.1	0.135	56.5	0.586	-36.1
1200	0.340	-151.4	1.763	72.7	0.153	60.6	0.581	-40.1

$V_{CE} = 3\text{ V}$, $I_C = 10\text{ mA}$, $Z_0 = 50\Omega$

Freq (MHz)	$ S_{11} $	$\angle S_{11}$	$ S_{21} $	$\angle S_{21}$	$ S_{12} $	$\angle S_{12}$	$ S_{22} $	$\angle S_{22}$
100	0.632	-59.2	11.508	135.2	0.031	63.9	0.811	-18.4
200	0.467	-92.6	7.923	115.1	0.045	58.7	0.677	-21.8
400	0.352	-129.6	4.570	95.5	0.067	61.8	0.584	-22.7
600	0.317	-147.2	3.190	85.3	0.089	65.4	0.561	-25.8
800	0.307	-157.8	2.432	78.1	0.109	68.6	0.548	-29.2
900	0.308	-162.6	2.217	75.1	0.122	69.1	0.551	-31.2
1000	0.314	-166.9	2.023	72.2	0.133	70.1	0.547	-33.3
1200	0.318	-172.2	1.756	67.0	0.156	70.1	0.549	-38.1

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